

IN THE SPECIFICATION

Please amend the indicated paragraph as follows:

β2 [0018] Depending on the specific process, the semiconductor wafer 190 can be heated to some desired temperature prior to material layer deposition. For example, wafer support 150 may be heated by an embedded heater element 170. The wafer support 150 may be resistively heated by applying an electric current from an AC power supply 106 to the heater element 170. The wafer 190 is, in turn, heated by the wafer support ~~190~~ 150. The wafer support 150 may be an electrostatic chuck.
